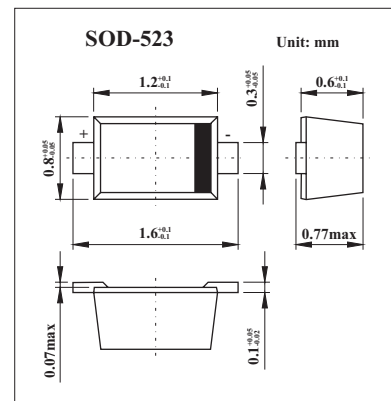


Schottky barrier diodes

1PS79SB63

■ Features

- Very low diode capacitance
- Very low forward voltage
- Ultra small SMD plastic packages.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Typ	Max	Unit
Continuous reverse voltage	V_R			5	V
Continuous forward current	I_F			20	mA
Junction temperature	T_j		0.5	125	$^\circ\text{C}$
Ambient temperature	T_{amb}	-65		+125	$^\circ\text{C}$
Storage temperature	T_{stg}	-65		+150	$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th(j-a)}$			450	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 0.1 \text{ mA}$		160	200	mV
		$I_F = 1 \text{ mA}$		240	300	
Reverse current	I_R	$V_R = 1 \text{ V}$		0.4	1	μA
		$V_R = 5 \text{ V}$			50	
Diode capacitance	C_d	$V_R = 0 \text{ V}; f = 1 \text{ MHz}$		0.35	0.5	pF
Series inductance	L_s			0.6		nH

Note

1. Pulse test: $t_p \leq 300 \mu\text{s}; \delta \leq 0.02$.

■ Marking

Marking	T1
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